
HM514170D, HM514270D Series HM51S4170D, HM51S4270D Series

262,144-word $\times$ 16-bit Dynamic RAM

HITACHI

ADE-203-672A (Z)

Rev. 1.0

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Description

The Hitachi HM51(S)4170D Series, HM51(S)4270D Series are CMOS dynamic RAM organized as 262,144-word $\times$ 16-bit. HM51(S)4170D Series, HM51(S)4270D Series have realized higher density, higher performance and various functions by employing 0.8 μ m CMOS process technology and some new CMOS circuit design technologies. The HM51(S)4170D Series, HM51(S)4270D Series offer fast page mode as a high speed access mode. They have the package variations of standard 40-pin plastic SOJ and standard 44-pin plastic TSOPII. Internal refresh timer enables HM51S4170D Series, HM51S4270D Series self refresh operation.

Features

- Single 5 V supply: 5 V $\pm$ 10%
- Access time: 60 ns/70 ns/80 ns (max)
- Power dissipation
 - Active mode
 - 743mW/660 mW/578 mW (max) (HM51(S)4170D Series)
 - 825 mW/770 mW/688 mW (max) (HM51(S)4270D Series)
 - Standby mode
 - 11 mW (max)
 - 1.1 mW (max) (L-version)
- Fast page mode capability
- Refresh cycles
 - 1024 refresh cycles
 - 16 ms (HM51(S)4170D Series)
 - 128 ms (L-version) (HM51(S)4170DL Series)
 - 512 refresh cycles
 - 8 ms (HM51(S)4270D Series)
 - 128 ms (L-version) (HM51(S)4270DL Series)
- 2 variations of refresh
 - $\overline{\text{RAS}}$ -only refresh

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— $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh

- 2 $\overline{\text{WE}}$ -byte control
- Self refresh operation (HM51S4170D, HM51S4270D)
- Battery backup operation (L-version)

Ordering Information

Type No.	Access time	Package
HM514170DJ-6	60 ns	400-mil 40-pin plastic SOJ (CP-40D)
HM514170DJ-7	70 ns	
HM514170DJ-8	80 ns	
HM514170DLJ-6	60 ns	
HM514170DLJ-7	70 ns	
HM514170DLJ-8	80 ns	
HM514270DJ-6	60 ns	
HM514270DJ-7	70 ns	
HM514270DJ-8	80 ns	
HM514270DLJ-6	60 ns	
HM514270DLJ-7	70 ns	
HM514270DLJ-8	80 ns	
HM51S4170DJ-6	60 ns	
HM51S4170DJ-7	70 ns	
HM51S4170DJ-8	80 ns	
HM51S4170DLJ-6	60 ns	
HM51S4170DLJ-7	70 ns	
HM51S4170DLJ-8	80 ns	
HM51S4270DJ-6	60 ns	
HM51S4270DJ-7	70 ns	
HM51S4270DJ-8	80 ns	
HM51S4270DLJ-6	60 ns	
HM51S4270DLJ-7	70 ns	
HM51S4270DLJ-8	80 ns	
HM514170DTT-6	60 ns	400-mil 44-pin plastic TSOP II (TTP-44/40DB)
HM514170DTT-7	70 ns	
HM514170DTT-8	80 ns	
HM514170DLTT-6	60 ns	
HM514170DLTT-7	70 ns	
HM514170DLTT-8	80 ns	
HM514270DTT-6	60 ns	
HM514270DTT-7	70 ns	
HM514270DTT-8	80 ns	
HM514270DLTT-6	60 ns	
HM514270DLTT-7	70 ns	
HM514270DLTT-8	80 ns	

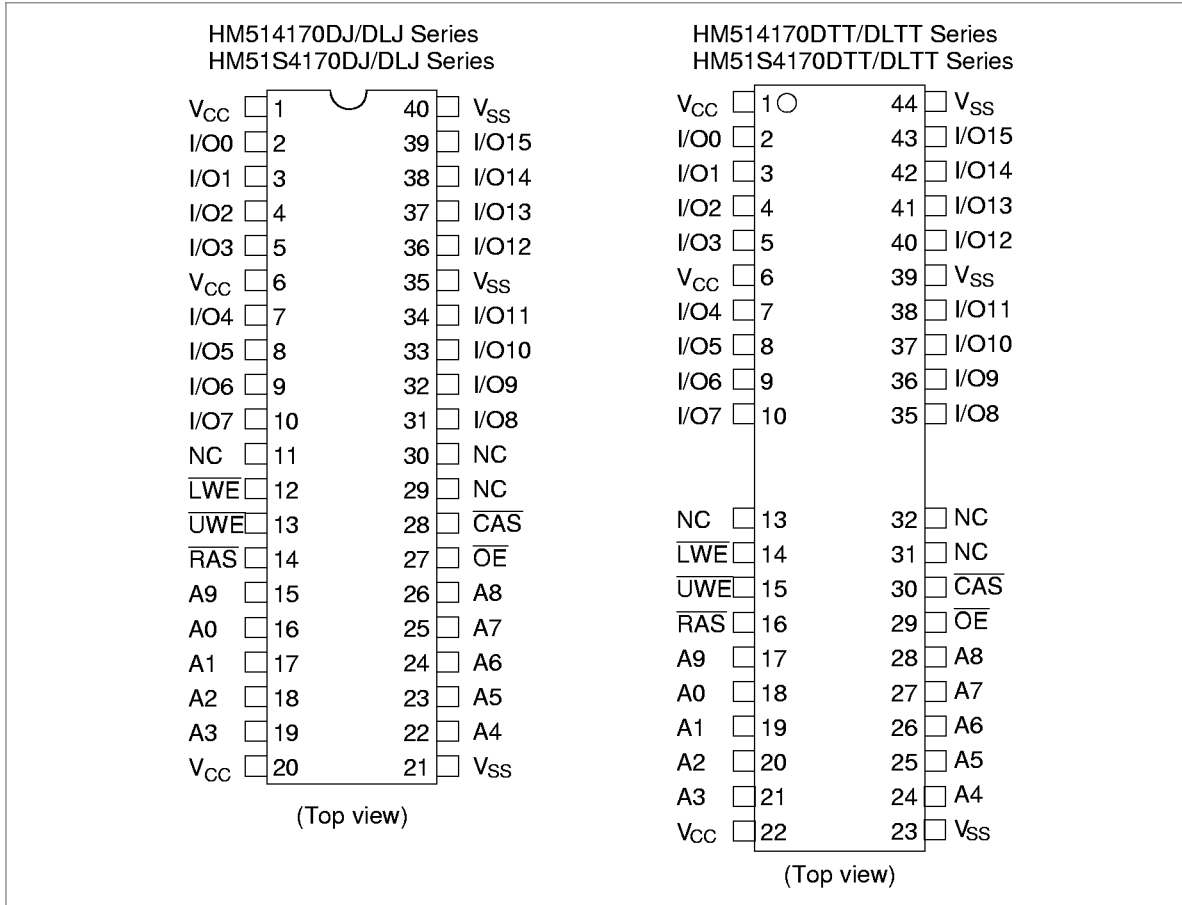
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Ordering Information (cont)

Type No.	Access time	Package
HM51S4170DTT-6	60 ns	400 mil 44-pin plastic TSOP II (TTP-44/40DB)
HM51S4170DTT-7	70 ns	
HM51S4170DTT-8	80 ns	
HM51S4170DLTT-6	60 ns	
HM51S4170DLTT-7	70 ns	
HM51S4170DLTT-8	80 ns	
HM51S4270DTT-6	60 ns	
HM51S4270DTT-7	70 ns	
HM51S4270DTT-8	80 ns	
HM51S4270DLTT-6	60 ns	
HM51S4270DLTT-7	70 ns	
HM51S4270DLTT-8	80 ns	

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Pin Arrangement

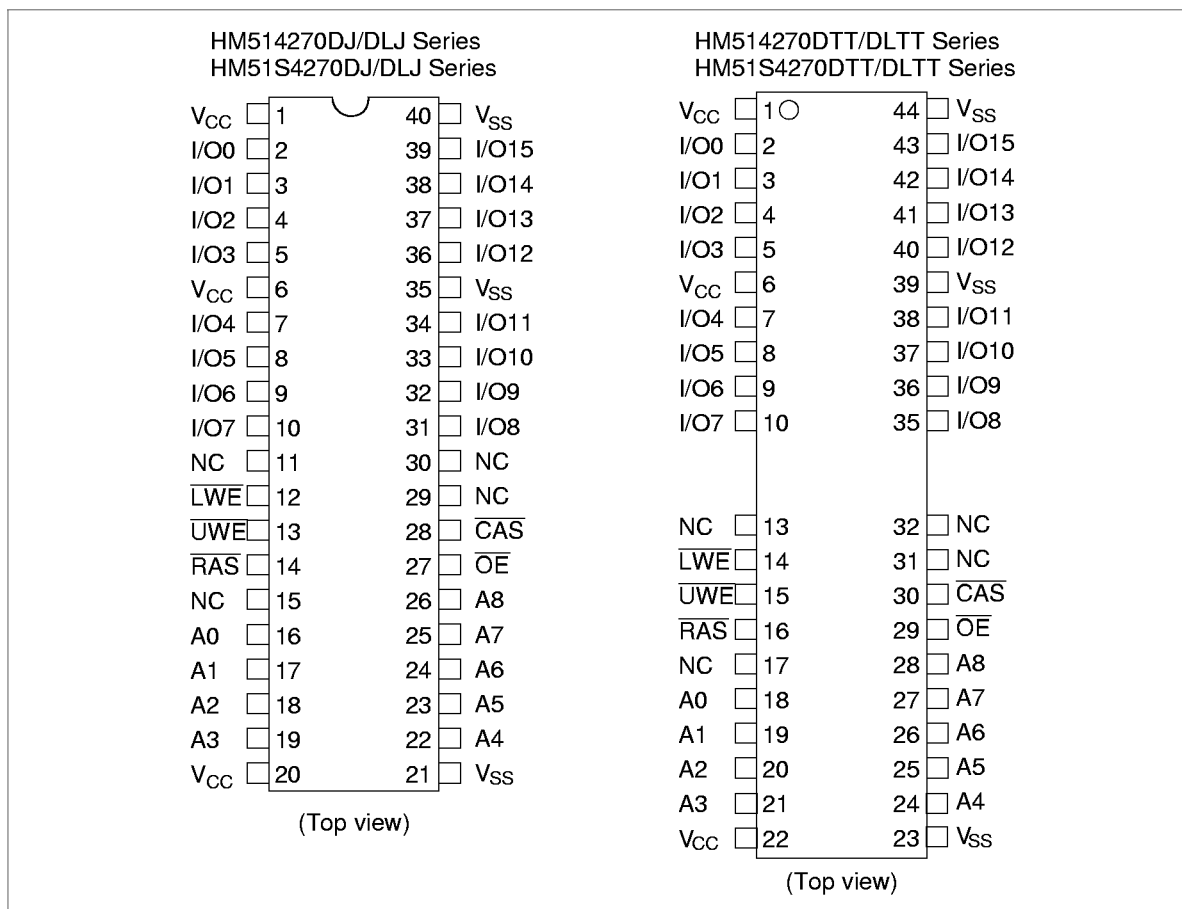


Pin Description

Pin name	Function
A0 to A9	Address input • Refresh address A0 to A9 • Row address A0 to A9 • Column address A0 to A7
I/O0 to I/O15	Data input/output
$\overline{\text{RAS}}$	Row address strobe
$\overline{\text{CAS}}$	Column address strobe
$\overline{\text{UWE}} / \overline{\text{LWE}}$	Read/write enable
$\overline{\text{OE}}$	Output enable
V _{CC}	Power supply
V _{SS}	Ground
NC	No connection

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Pin Arrangement

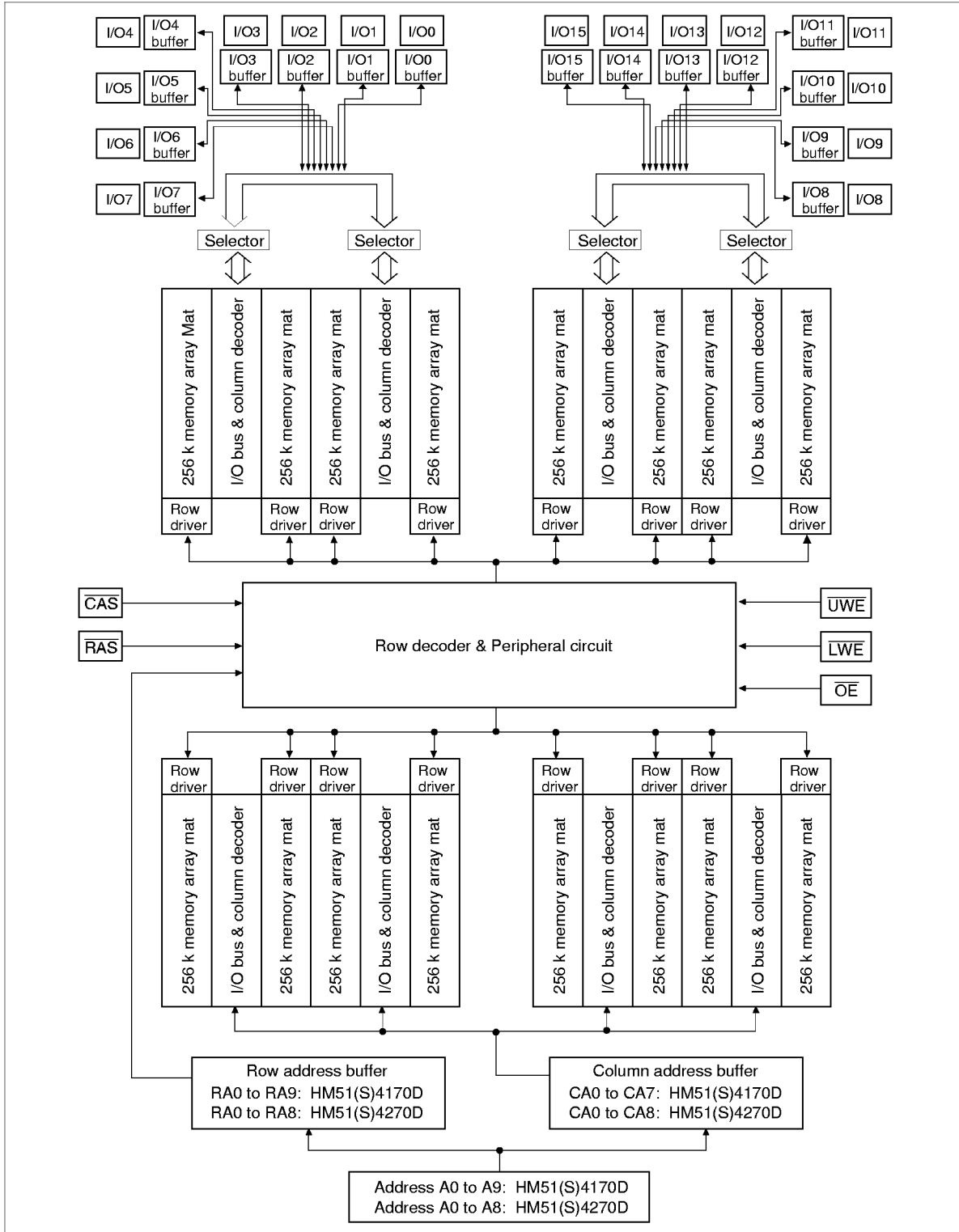


Pin Description

Pin name	Function
A0 to A8	Address input • Refresh address A0 to A8 • Row address A0 to A8 • Column address A0 to A8
I/O0 to I/O15	Data input/output
$\overline{\text{RAS}}$	Row address strobe
$\overline{\text{CAS}}$	Column address strobe
$\overline{\text{UWE}} / \overline{\text{LWE}}$	Read/write enable
$\overline{\text{OE}}$	Output enable
V _{CC}	Power supply
V _{SS}	Ground
NC	No connection

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Block Diagram



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Operation Table

The HM51(S)4170D, HM51(S)4270D series has the following 11 operation modes.

1. Read cycle
2. Early write cycle
3. Delayed write cycle
4. Read-modify-write cycle
5. $\overline{\text{RAS}}$ -only refresh cycle
6. $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycle
7. Self refresh cycle (HM51S4170D, HM51S4270D)
8. Fast page mode read cycle
9. Fast page mode early write cycle
10. Fast page mode delayed write cycle
11. Fast page mode read-modify-write cycle

Inputs

$\overline{\text{RAS}}$	$\overline{\text{CAS}}$	$\overline{\text{UWE}}$	$\overline{\text{LWE}}$	$\overline{\text{OE}}$	Output	Operation
H	H	D	D	D	Open	Standby
H	L	H	H	L	Valid	Standby
L	L	H	H	L	Valid	Read cycle
L	L	L ^{*2}	L ^{*2}	D	Open	Early write cycle
L	L	L ^{*2}	L ^{*2}	H	Undefined	Delayed write cycle
L	L	H to L	H to L	L to H	Valid	Read-modify-write cycle
L	H	D	D	D	Open	$\overline{\text{RAS}}$ -only refresh cycle
H to L	L	D	D	D	Open	$\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh cycle Self refresh cycle
L	H to L	H	H	L	Valid	Fast page mode read cycle
L	H to L	L ^{*2}	L ^{*2}	D	Open	Fast page mode early write cycle
L	H to L	L ^{*2}	L ^{*2}	H	Undefined	Fast page mode delayed write cycle
L	H to L	H to L	H to L	L to H	Valid	Fast page mode read modify-write cycle

Notes: 1. H: High(inactive) L: Low(active) D: H or L (H: $V_{IH}(\min) \leq V_{IN} \leq V_{IH}(\max)$, L: $V_{IL}(\min) \leq V_{IN} \leq V_{IL}(\max)$)

2. $t_{WCS} \geq 0$ ns: Early write cycle
 $t_{WCS} < 0$ ns: Delayed write cycle

3. Mode is determined by the OR function of the $\overline{\text{UWE}}$ and $\overline{\text{LWE}}$. (Mode is set by the earliest of $\overline{\text{UWE}}$ and $\overline{\text{LWE}}$ active edge and reset by the latest of $\overline{\text{UWE}}$ and $\overline{\text{LWE}}$ inactive edge.) However write operation and output High-Z control are done independently by each $\overline{\text{UWE}}$, $\overline{\text{LWE}}$.

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Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Voltage on any pin relative to V_{SS}	V_T	-1.0 to +7.0	V
Supply voltage relative to V_{SS}	V_{CC}	-1.0 to +7.0	V
Short circuit output current	I_{out}	50	mA
Power dissipation	P_T	1.0	W
Operating temperature range	T_{opr}	0 to +70	°C
Storage temperature range	T_{stg}	-55 to +125	°C

Recommended DC Operating Conditions ($T_a = 0$ to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit	Notes
Supply voltage	V_{SS}	0	0	0	V	2
	V_{CC}	4.5	5.0	5.5	V	1, 2
Input high voltage	V_{IH}	2.4	—	6.5	V	1
Input low voltage	V_{IL}	-1.0	—	0.8	V	1

Notes: 1. All voltage referred to V_{SS} .

2. The supply voltage with all V_{CC} pins must be on the same level.

The supply voltage with all V_{SS} pins must be on the same level.

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DC Characteristics

($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$)*⁵ (HM51(S)4170D Series)

		HM514170D, HM51S4170D							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Test conditions
Operating current* ^{1, *2}	I_{CC1}	—	135	—	120	—	105	mA	$\overline{\text{RAS}}$, $\overline{\text{CAS}}$ cycling, $t_{RC} = \min$
Standby current	I_{CC2}	—	2	—	2	—	2	mA	TTL interface, $\overline{\text{RAS}}$, $\overline{\text{CAS}} = V_{IH}$ Dout = High-Z
		—	1	—	1	—	1	mA	CMOS interface $\overline{\text{RAS}}$, $\overline{\text{CAS}}$, $\overline{\text{UWE}}$, $\overline{\text{LWE}}$, $\overline{\text{OE}}$ $\geq V_{CC} - 0.2\text{ V}$ Dout = High-Z
Standby current (L-version)	I_{CC2}	—	200	—	200	—	200	μA	CMOS interface $\overline{\text{RAS}}$, $\overline{\text{CAS}}$, $\overline{\text{OE}}$, $\overline{\text{UWE}}$, $\overline{\text{LWE}} \geq V_{CC} - 0.2\text{ V}$ Dout = High-Z
$\overline{\text{RAS}}$ -only refresh current* ²	I_{CC3}	—	135	—	120	—	100	mA	$t_{RC} = \min$
$\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh current* ²	I_{CC6}	—	135	—	120	—	100	mA	$t_{RC} = \min$
Fast page mode current* ^{1, *3}	I_{CC7}	—	150	—	120	—	100	mA	$t_{PC} = \min$
Battery backup current* ⁴ (Standby with CBR refresh) (L-version)	I_{CC10}	—	300	—	300	—	300	μA	Standby: CMOS interface Dout = High-Z CBR refresh: $t_{RC} = 125\text{ }\mu\text{s}$ $t_{RAS} \leq 1\text{ }\mu\text{s}$, $\overline{\text{CAS}} = V_{IL}$ $\overline{\text{LWE}}$, $\overline{\text{UWE}}$, $\overline{\text{OE}} = V_{IH}$
Self-refresh mode current (HM51S4170D)	I_{CC11}	—	1	—	1	—	1	mA	CMOS interface $\overline{\text{RAS}}$, $\overline{\text{CAS}} \leq 0.2\text{ V}$, Dout = High-Z
Self-refresh mode current (HM51S4170DL)	I_{CC11}	—	200	—	200	—	200	μA	CMOS interface $\overline{\text{RAS}}$, $\overline{\text{CAS}} \leq 0.2\text{ V}$ Dout = High-Z
Input leakage current	I_{LI}	-10	10	-10	10	-10	10	μA	$0\text{ V} \leq V_{in} \leq 6.5\text{ V}$
Output leakage current	I_{LO}	-10	10	-10	10	-10	10	μA	$0\text{ V} \leq V_{out} \leq 6.5\text{ V}$ Dout = disable
Output high voltage	V_{OH}	2.4	V_{CC}	2.4	V_{CC}	2.4	V_{CC}	V	High Iout = -5.0 mA
Output low voltage	V_{OL}	0	0.4	0	0.4	0	0.4	V	Low Iout = 4.2 mA

Notes: 1. I_{CC} depends on output load condition when the device is selected. I_{CC} max is specified at the output open condition.

2. Address can be changed once or less while $\overline{\text{RAS}} = V_{IL}$.

3. Address can be changed once or less while $\overline{\text{CAS}} = V_{IH}$.

4. $V_{IH} \geq V_{CC} - 0.2\text{ V}$, $0 \leq V_{IL} \leq 0.2\text{ V}$, Address can be changed once or less while $\overline{\text{RAS}} = V_{IL}$.

5. All the V_{CC} pins shall be supplied with the same voltage. And all the V_{SS} pins shall be supplied with the same voltage.

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DC Characteristics

($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$)*⁵ (HM51(S)4270D Series)

		HM514270D, HM51S4270D							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Test conditions
Operating current*1, *2	I _{CC1}	—	150	—	140	—	125	mA	$\overline{\text{RAS}}$, $\overline{\text{CAS}}$ cycling, t _{RC} = min
Standby current	I _{CC2}	—	2	—	2	—	2	mA	TTL interface, $\overline{\text{RAS}}$, $\overline{\text{CAS}}$ = V _{IH} Dout = High-Z
		—	1	—	1	—	1	mA	CMOS interface $\overline{\text{RAS}}$, $\overline{\text{CAS}}$, $\overline{\text{UWE}}$, $\overline{\text{LWE}}$, $\overline{\text{OE}}$ ≥ V _{CC} − 0.2 V Dout = High-Z
Standby current (L-version)	I _{CC2}	—	200	—	200	—	200	μA	CMOS interface $\overline{\text{RAS}}$, $\overline{\text{CAS}}$, $\overline{\text{OE}}$, $\overline{\text{UWE}}$, $\overline{\text{LWE}}$ ≥ V _{CC} − 0.2 V Dout = High-Z
$\overline{\text{RAS}}$ -only refresh current*2	I _{CC3}	—	140	—	130	—	110	mA	t _{RC} = min
$\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ refresh current*2	I _{CC6}	—	140	—	130	—	110	mA	t _{RC} = min
Fast page mode current*1, *3	I _{CC7}	—	150	—	130	—	120	mA	t _{PC} = min
Battery backup current*4 (Standby with CBR refresh) (L-version)	I _{CC10}	—	300	—	300	—	300	μA	Standby: CMOS interface Dout = High-Z CBR refresh: t _{RC} = 250 μs t _{RAS} ≤ 1 μs, $\overline{\text{CAS}}$ = V _{IL} $\overline{\text{LWE}}$, $\overline{\text{UWE}}$, $\overline{\text{OE}}$ = V _{IH}
Self-refresh mode current (HM51S4270D)	I _{CC11}	—	1	—	1	—	1	mA	CMOS interface $\overline{\text{RAS}}$, $\overline{\text{CAS}}$ ≤ 0.2 V, Dout = High-Z
Self-refresh mode current (HM51S4270DL)	I _{CC11}	—	200	—	200	—	200	μA	CMOS interface $\overline{\text{RAS}}$, $\overline{\text{CAS}}$ ≤ 0.2 V Dout = High-Z
Input leakage current	I _{LI}	−10	10	−10	10	−10	10	μA	0 V ≤ Vin ≤ 6.5 V
Output leakage current	I _{LO}	−10	10	−10	10	−10	10	μA	0 V ≤ Vout ≤ 6.5 V Dout = disable
Output high voltage	V _{OH}	2.4	V _{CC}	2.4	V _{CC}	2.4	V _{CC}	V	High Iout = −5.0 mA
Output low voltage	V _{OL}	0	0.4	0	0.4	0	0.4	V	Low Iout = 4.2 mA

Notes: 1. I_{CC} depends on output load condition when the device is selected. I_{CC} max is specified at the output open condition.

2. Address can be changed once or less while $\overline{\text{RAS}} = V_{IL}$.

3. Address can be changed once or less while $\overline{\text{CAS}} = V_{IH}$.

4. $V_{IH} \geq V_{CC} - 0.2\text{ V}$, $0 \leq V_{IL} \leq 0.2\text{ V}$, Address can be changed once or less while $\overline{\text{RAS}} = V_{IL}$.

5. All the V_{CC} pins shall be supplied with the same voltage. And all the V_{SS} pins shall be supplied with the same voltage.

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Capacitance ($T_a = 25^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$)

Parameter	Symbol	Typ	Max	Unit	Notes
Input capacitance (Address)	C_{I1}	—	5	pF	1
Input capacitance (Clocks)	C_{I2}	—	7	pF	1
Output capacitance (Data-in, Data-out)	$C_{I/O}$	—	10	pF	1, 2

Notes: 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.

2. $\overline{\text{CAS}} = V_{IH}$ to disable Dout.

AC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$)*¹, *¹⁴, *¹⁵, *¹⁷, *¹⁸

Test Conditions

- Input rise and fall time: 5 ns
- Input timing reference levels: 0.8 V, 2.4 V
- Input levels: 0 V, 3 V
- Output load: 2 TTL gate + C_L (100 pF) (Including scope and jig)

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Read, Write, Read-Modify-Write and Refresh Cycles (Common Parameters)

		HM514170D, HM51S4170D HM514270D, HM51S4270D							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Random read or write cycle time	t _{RC}	110	—	130	—	150	—	ns	
RAS precharge time	t _{RP}	40	—	50	—	60	—	ns	
RAS pulse width	t _{RAS}	60	10000	70	10000	80	10000	ns	
CAS pulse width	t _{CAS}	15	10000	20	10000	20	10000	ns	22
Row address setup time	t _{ASR}	0	—	0	—	0	—	ns	
Row address hold time	t _{RAH}	10	—	10	—	10	—	ns	
Column address setup time	t _{ASC}	0	—	0	—	0	—	ns	
Column address hold time	t _{CAH}	15	—	15	—	15	—	ns	
RAS to CAS delay time	t _{RCD}	20	45	20	50	20	60	ns	8
RAS to column address delay time	t _{RAD}	15	30	15	35	15	40	ns	9
RAS hold time	t _{RSH}	15	—	20	—	20	—	ns	
CAS hold time	t _{CSH}	60	—	70	—	80	—	ns	
CAS to RAS precharge time	t _{CRP}	10	—	15	—	15	—	ns	
OE to Din delay time	t _{ODD}	15	—	20	—	20	—	ns	
OE delay time from Din	t _{DZO}	0	—	0	—	0	—	ns	
CAS setup time from Din	t _{DZC}	0	—	0	—	0	—	ns	
Transition time (rise and fall)	t _T	3	50	3	50	3	50	ns	7

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Read Cycle

		HM514170D, HM51S4170D HM514270D, HM51S4270D							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Access time from $\overline{\text{RAS}}$	t_{RAC}	—	60	—	70	—	80	ns	2, 3
Access time from $\overline{\text{CAS}}$	t_{CAC}	—	15	—	20	—	20	ns	3, 4, 13
Access time from address	t_{AA}	—	30	—	35	—	40	ns	3, 5, 13
Access time from $\overline{\text{OE}}$	t_{OAC}	—	15	—	20	—	20	ns	3, 22
Read command setup time	t_{RCS}	0	—	0	—	0	—	ns	20
Read command hold time to $\overline{\text{CAS}}$	t_{RCH}	0	—	0	—	0	—	ns	16, 19
Read command hold time to $\overline{\text{RAS}}$	t_{RRH}	0	—	0	—	0	—	ns	16, 19
Column address to $\overline{\text{RAS}}$ lead time	t_{RAL}	30	—	35	—	40	—	ns	
Output buffer turn-off time	t_{OFF1}	0	15	0	15	0	15	ns	6
Output buffer turn-off to $\overline{\text{OE}}$	t_{OFF2}	0	15	0	15	0	15	ns	6
$\overline{\text{CAS}}$ to Din delay time	t_{CDD}	15	—	15	—	15	—	ns	

Write Cycle

		HM514170D, HM51S4170D HM514270D, HM51S4270D							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Write command setup time	t_{WCS}	0	—	0	—	0	—	ns	10, 19
Write command hold time	t_{WCH}	15	—	15	—	15	—	ns	20
Write command pulse width	t_{WP}	10	—	10	—	10	—	ns	21
Write command to $\overline{\text{RAS}}$ lead time	t_{RWL}	15	—	20	—	20	—	ns	21
Write command to $\overline{\text{CAS}}$ lead time	t_{CWL}	15	—	20	—	20	—	ns	21
Data-in setup time	t_{DS}	0	—	0	—	0	—	ns	11, 21
Data-in hold time	t_{DH}	15	—	15	—	15	—	ns	11, 21
$\overline{\text{CAS}}$ to $\overline{\text{OE}}$ delay time	t_{COD}	—	0	—	0	—	0	ns	22

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Read-Modify-Write Cycle

		HM514170D, HM51S4170D HM514270D, HM51S4270D							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Read-modify-write cycle time	t_{RWC}	150	—	180	—	200	—	ns	
$\overline{RAS}$ to $\overline{WE}$ delay time	t_{RWD}	80	—	95	—	105	—	ns	10, 19
$\overline{CAS}$ to $\overline{WE}$ delay time	t_{CWD}	35	—	45	—	45	—	ns	10, 19
Column address to $\overline{WE}$ delay time	t_{AWD}	50	—	60	—	65	—	ns	10, 19
$\overline{OE}$ hold time from $\overline{WE}$	t_{OEh}	15	—	20	—	20	—	ns	21

Refresh Cycle

		HM514170D, HM51S4170D HM514270D, HM51S4270D							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
$\overline{CAS}$ setup time (CBR refresh cycle)	t_{CSR}	10	—	10	—	10	—	ns	19
$\overline{CAS}$ hold time (CBR refresh cycle)	t_{CHR}	10	—	10	—	10	—	ns	20
$\overline{RAS}$ precharge to $\overline{CAS}$ hold time	t_{RPC}	10	—	10	—	10	—	ns	19
$\overline{CAS}$ precharge time in normal mode	t_{CPN}	10	—	10	—	10	—	ns	

Fast Page Mode Cycle

		HM514170D, HM51S4170D HM514270D, HM51S4270D							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Fast page mode cycle time	t_{PC}	40	—	45	—	50	—	ns	
Fast page mode $\overline{CAS}$ precharge time	t_{CP}	10	—	10	—	10	—	ns	
Fast page mode $\overline{RAS}$ pulse width	t_{RASC}	—	100000	—	100000	—	100000	ns	12
Access time from $\overline{CAS}$ precharge	t_{ACP}	—	35	—	40	—	45	ns	3, 13
$\overline{RAS}$ hold time from $\overline{CAS}$ precharge	t_{RHCP}	35	—	40	—	45	—	ns	

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Fast Page Mode Read-Modify-Write Cycle

		HM514170D, HM51S4170D HM514270D, HM51S4270D							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
CAS precharge to $\overline{\text{UWE}}$, $\overline{\text{LWE}}$ delay time	t_{CPW}	55	—	65	—	70	—	ns	10, 21
Fast page mode read-modify-write cycle time	t_{PCM}	80	—	95	—	100	—	ns	

Refresh (HM51(S)4170D Series)

Parameter	Symbol	Max	Unit	Notes
Refresh period	t_{REF}	16	ms	1024 cycles
Refresh period (L-version)	t_{REF}	128	ms	1024 cycles

Refresh (HM51(S)4270D Series)

Parameter	Symbol	Max	Unit	Notes
Refresh period	t_{REF}	8	ms	512 cycles
Refresh period (L-version)	t_{REF}	128	ms	512 cycles

HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

Self Refresh Mode

		HM51S4170D, HM51S4270D							
		-6		-7		-8			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
RAS pulse width (self refresh)	t _{RASS}	100	—	100	—	100	—	μs	23, 24, 25, 26
$\overline{\text{RAS}}$ precharge time (self refresh)	t _{RPS}	110	—	130	—	150	—	ns	
$\overline{\text{CAS}}$ hold time (self refresh)	t _{CHS}	−50	—	−50	—	−50	—	ns	

- Notes:
1. AC measurements assume $t_T = 5 \text{ ns}$. $V_{\text{IH}} = 3.0 \text{ V}$, $V_{\text{IL}} = 0.0 \text{ V}$.
 2. Assumes that $t_{\text{RCD}} \leq t_{\text{RCD}} (\text{max})$ and $t_{\text{RAD}} \leq t_{\text{RAD}} (\text{max})$. If t_{RCD} or t_{RAD} is greater than the maximum recommended value shown in this table, t_{RAC} exceeds the value shown.
 3. Measured with a load circuit equivalent to 2 TTL loads and 100 pF.
 4. Assumes that $t_{\text{RCD}} \geq t_{\text{RCD}} (\text{max})$ and $t_{\text{RAD}} \leq t_{\text{RAD}} (\text{max})$.
 5. Assumes that $t_{\text{RCD}} \leq t_{\text{RCD}} (\text{max})$ and $t_{\text{RAD}} \geq t_{\text{RAD}} (\text{max})$.
 6. $t_{\text{OFF}} (\text{max})$ defines the time at which the output achieves the open circuit condition and is not referred to output voltage levels.
 7. $V_{\text{IH}} (\text{min})$ and $V_{\text{IL}} (\text{max})$ are reference levels for measuring timing of input signals. Also, transition times are measured between V_{IH} and V_{IL} .
 8. Operation with the $t_{\text{RCD}} (\text{max})$ limit insures that $t_{\text{RAC}} (\text{max})$ can be met, $t_{\text{RCD}} (\text{max})$ is specified as a reference point only, if t_{RCD} is greater than the specified $t_{\text{RCD}} (\text{max})$ limit, then access time is controlled exclusively by t_{CAC} .
 9. Operation with the $t_{\text{RAD}} (\text{max})$ limit insures that $t_{\text{RAC}} (\text{max})$ can be met, $t_{\text{RAD}} (\text{max})$ is specified as a reference point only, if t_{RAD} is greater than the specified $t_{\text{RAD}} (\text{max})$ limit, then access time is controlled exclusively by t_{AA} .
 10. t_{WCS} , t_{RWD} , t_{CWD} and t_{AWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only: if $t_{\text{WCS}} \geq t_{\text{WCS}} (\text{min})$, the cycle is an early write cycle and the data out pin will remain open circuit (high impedance) throughout the entire cycle; if $t_{\text{RWD}} \geq t_{\text{RWD}} (\text{min})$, $t_{\text{CWD}} \geq t_{\text{CWD}} (\text{min})$, $t_{\text{AWD}} \geq t_{\text{AWD}} (\text{min})$ and $t_{\text{CPW}} \geq t_{\text{CPW}} (\text{min})$, the cycle is a read-modify-write and the data output will contain data read from the selected cell; if neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
 11. These parameters are referred to $\overline{\text{CAS}}$ leading edge in an early write cycle and to $\overline{\text{WE}}$ leading edge in a delayed write or a read-modify-write cycle.
 12. t_{RASC} defines RAS pulse width in fast page mode cycles.
 13. Access time is determined by the longest among t_{AA} , t_{CAC} and t_{ACP} .
 14. After power up pause for 100 μs , then DRAM initialization requires a minimum of eight $\overline{\text{RAS}}$ -only refresh or eight CAS-before- $\overline{\text{RAS}}$ refresh cycles. If the user will implement CAS-before- $\overline{\text{RAS}}$ timing in their system, then the eight initialization cycles MUST be CAS-before- $\overline{\text{RAS}}$ cycles.
 15. In delayed write or read-modify-write cycles, $\overline{\text{OE}}$ must disable output buffer prior to applying data to the device.
 16. Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.
 17. The supply voltage with all V_{CC} pins must be on the same level.
The supply voltage with all V_{SS} pins must be on the same level.
 18. A word of data can be written only when $\overline{\text{UWE}}$ and $\overline{\text{LWE}}$ go low at the same time. This implies that early write cycles cannot be combined with delayed write cycles in the same cycles because all data is latched at the fall of the first $\overline{\text{WE}}$. In other words, staggering the $\overline{\text{WE}}$ signals in one cycle is not permitted.
 19. t_{RCH} , t_{RRH} , t_{WCS} , t_{RWD} , t_{CWD} , t_{RPC} , t_{CSR} and t_{AWD} are determined by the earlier falling edge of $\overline{\text{UWE}}$ and $\overline{\text{LWE}}$.

HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

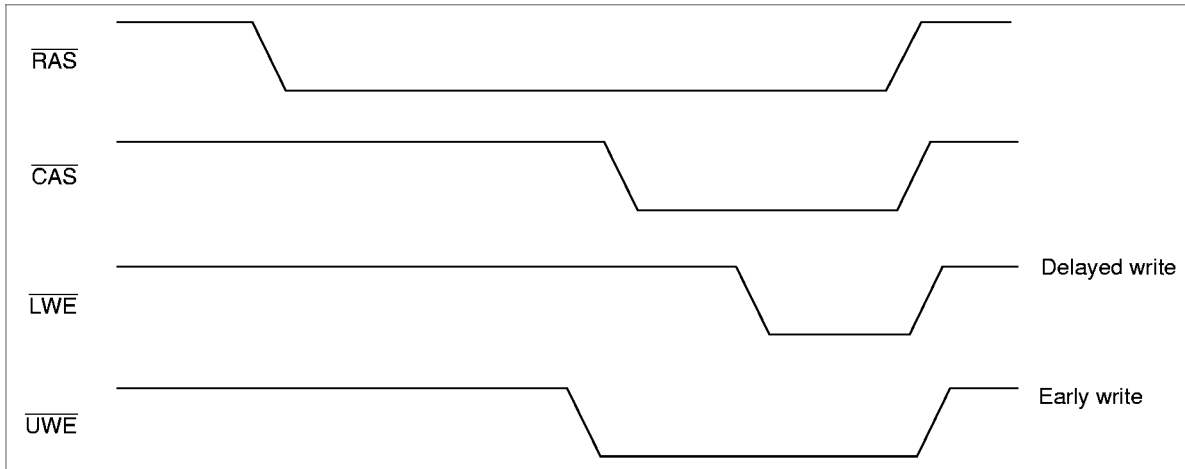
20. t_{WCH} , t_{RCS} and t_{CHR} are determined by the later rising edge of $\overline{UWE}$ or $\overline{LWE}$.
21. t_{WP} , t_{RWL} , t_{CWL} , t_{OEHL} , t_{DS} , t_{DH} and t_{CPW} should be satisfied by both $\overline{UWE}$ and $\overline{LWE}$.
22. When output buffers are enabled once, sustain the low impedance state until valid data is obtained. When output buffer is turned on and off within a very short time, generally it causes large V_{CC}/V_{SS} line noise, which causes to degrade V_{IH} (min)/ V_{IL} (max) level.
23. Please do not use t_{RASS} timing, $10\ \mu s \leq t_{RASS} \leq 100\ \mu s$. During this period, the device is in transition state from normal operation mode to self refresh mode. If $t_{RASS} > 100\ \mu s$, then $\overline{RAS}$ precharge time should use t_{RPS} instead of t_{RP} .
24. If you use distributed CBR refresh mode with $15.6\ \mu s$ interval in normal read/write cycle, CBR refresh should be executed within $15.6\ \mu s$ immediately after exiting from and before entering into self refresh mode.
25. If you use $\overline{RAS}$ only refresh or CBR burst refresh mode in normal read/write cycle, 1024 or 512 cycles (1024 cycles: HM51S4170D Series, 512 cycles: HM51S4270D Series) of distributed CBR refresh with $15.6\ \mu s$ interval should be executed within 16 or 8 ms (16 ms: HM51S4170D Series, 8 ms: HM51S4270D Series) immediately after exiting from and before entering into the self refresh mode.
26. Repetitive self refresh mode without refreshing all memory is not allowed. Once you exit from self refresh mode, all memory cells need to be refreshed before re-entering the self refresh mode again.
27. XXX: H or L (H: V_{IH} (min) $\leq V_{IN} \leq V_{IH}$ (max), L: V_{IL} (min) $\leq V_{IN} \leq V_{IL}$ (max))
/////: Invalid Dout
When the address, clock and input pins are not described on timing waveforms, their pins must be applied V_{IH} or V_{IL} .

HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

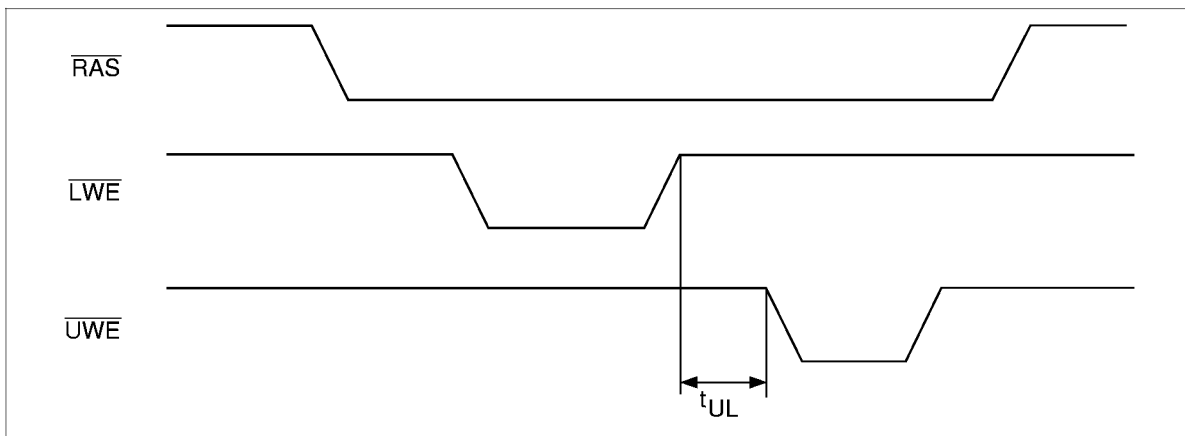
Notes concerning $\overline{2WE}$ control

Please do not separate the $\overline{UWE}/\overline{LWE}$ operation timing intentionally. However skew between $\overline{UWE}/\overline{LWE}$ are allowed under the following conditions.

1. Each of the $\overline{UWE}/\overline{LWE}$ should satisfy the timing specifications individually.
2. Different operation mode for upper/lower byte is not allowed; such as following.

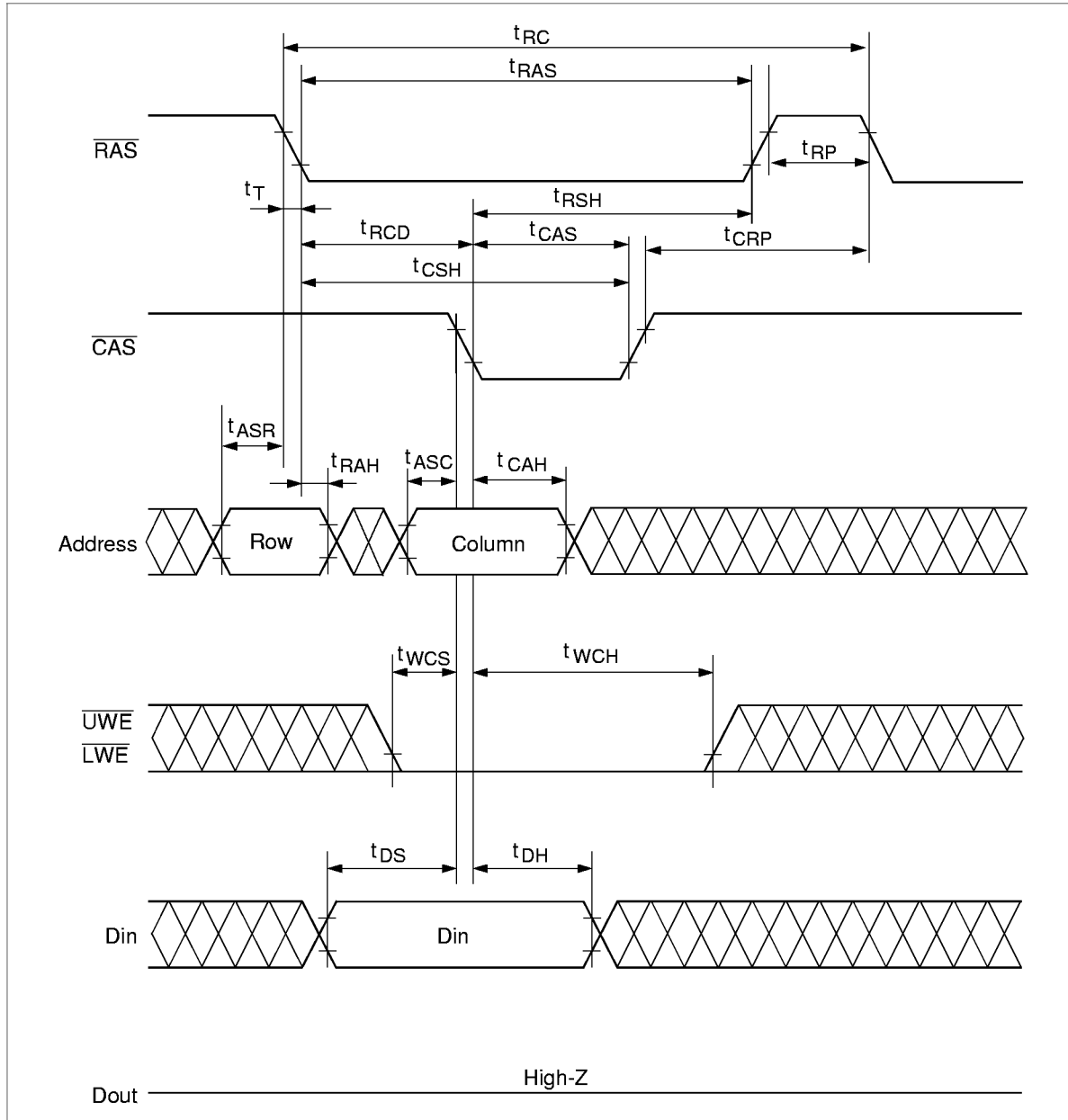


3. Closely separated upper/lower byte control is not allowed, unless the condition ($t_{CP} \leq t_{UL}$) is satisfied.



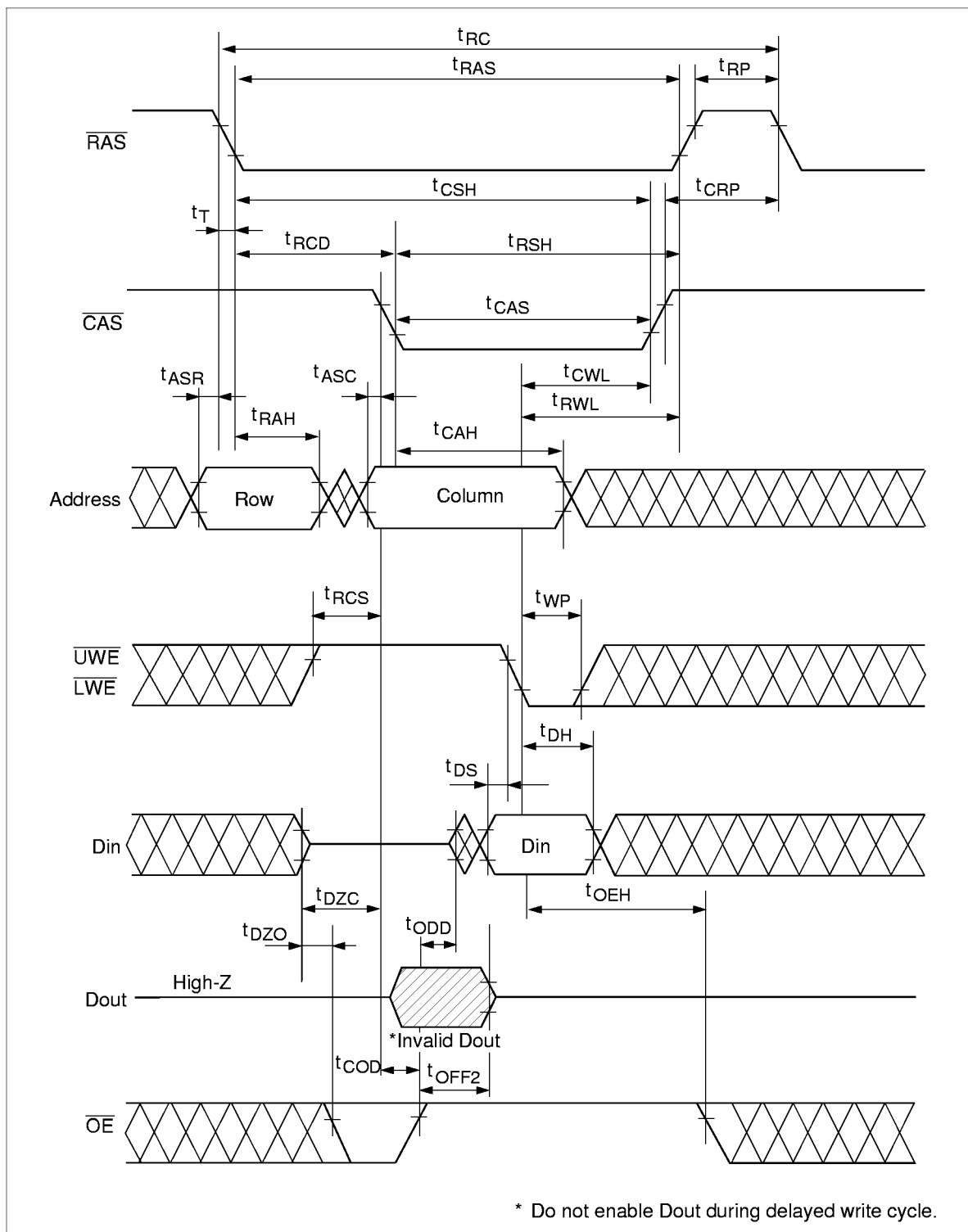
HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

Early Write Cycle



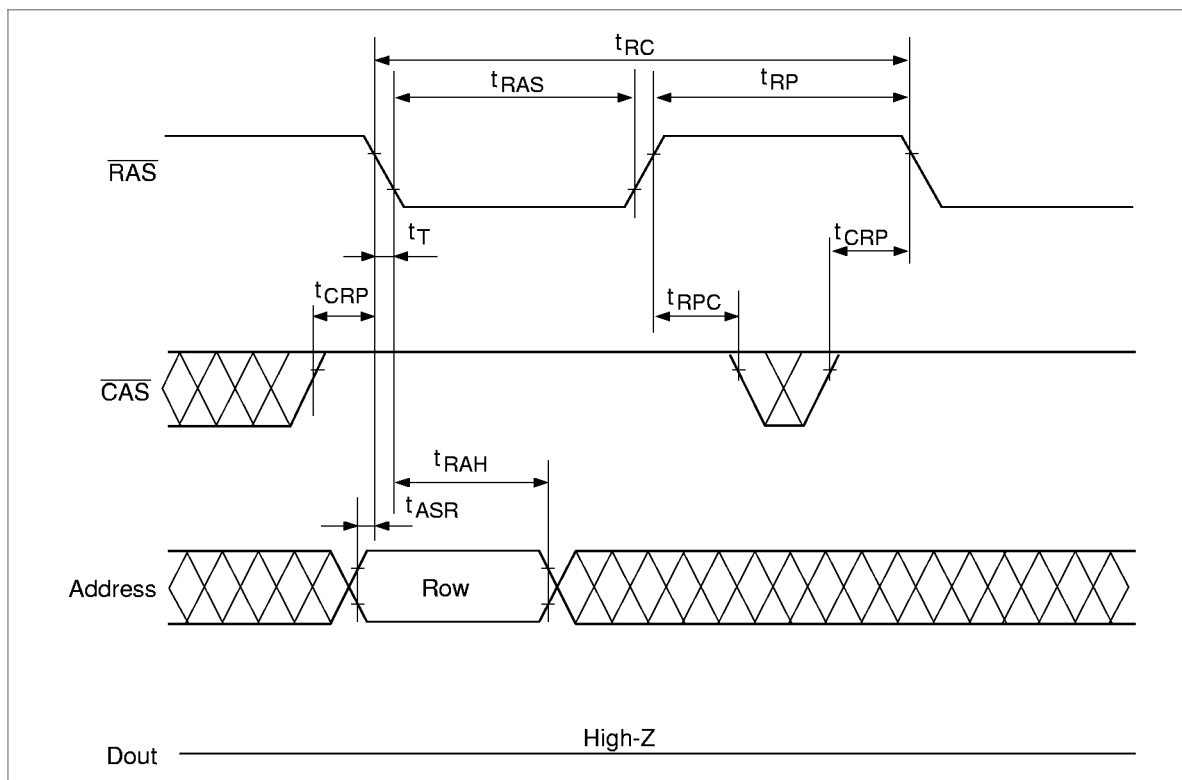
HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

Delayed Write Cycle



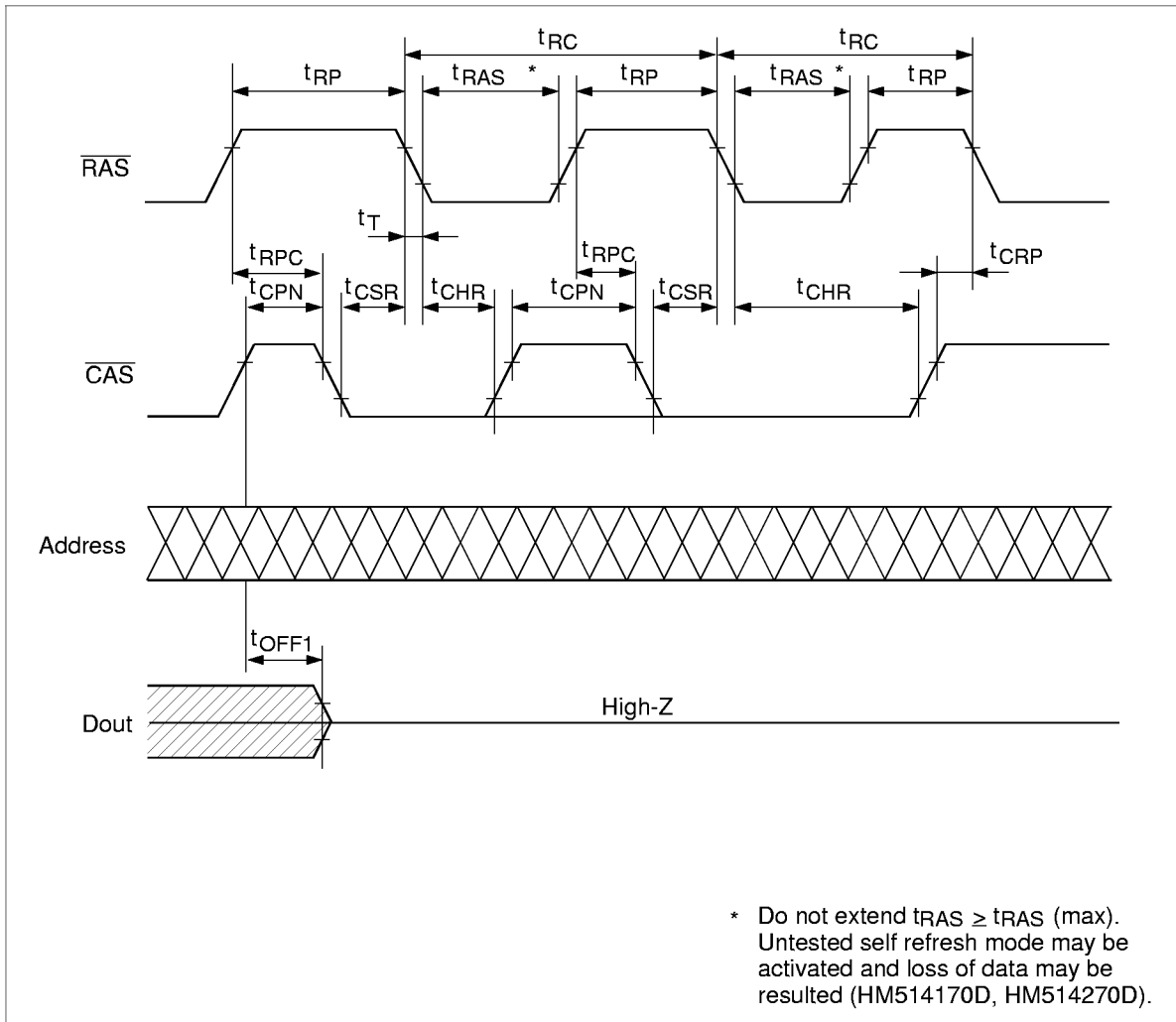
HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

$\overline{\text{RAS}}$ -Only Refresh Cycle

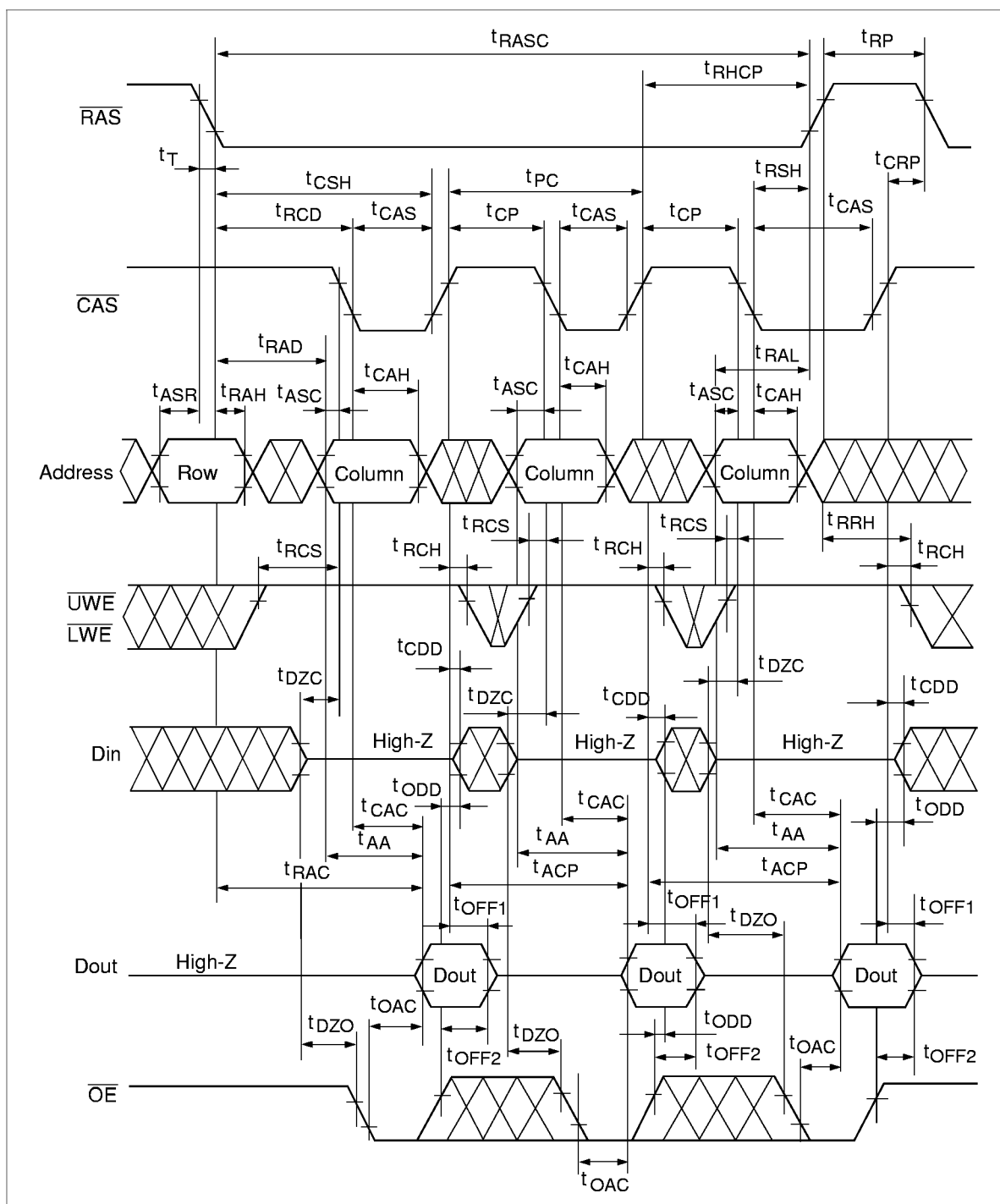


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$\overline{\text{CAS}}$ -Before- $\overline{\text{RAS}}$ Refresh Cycle

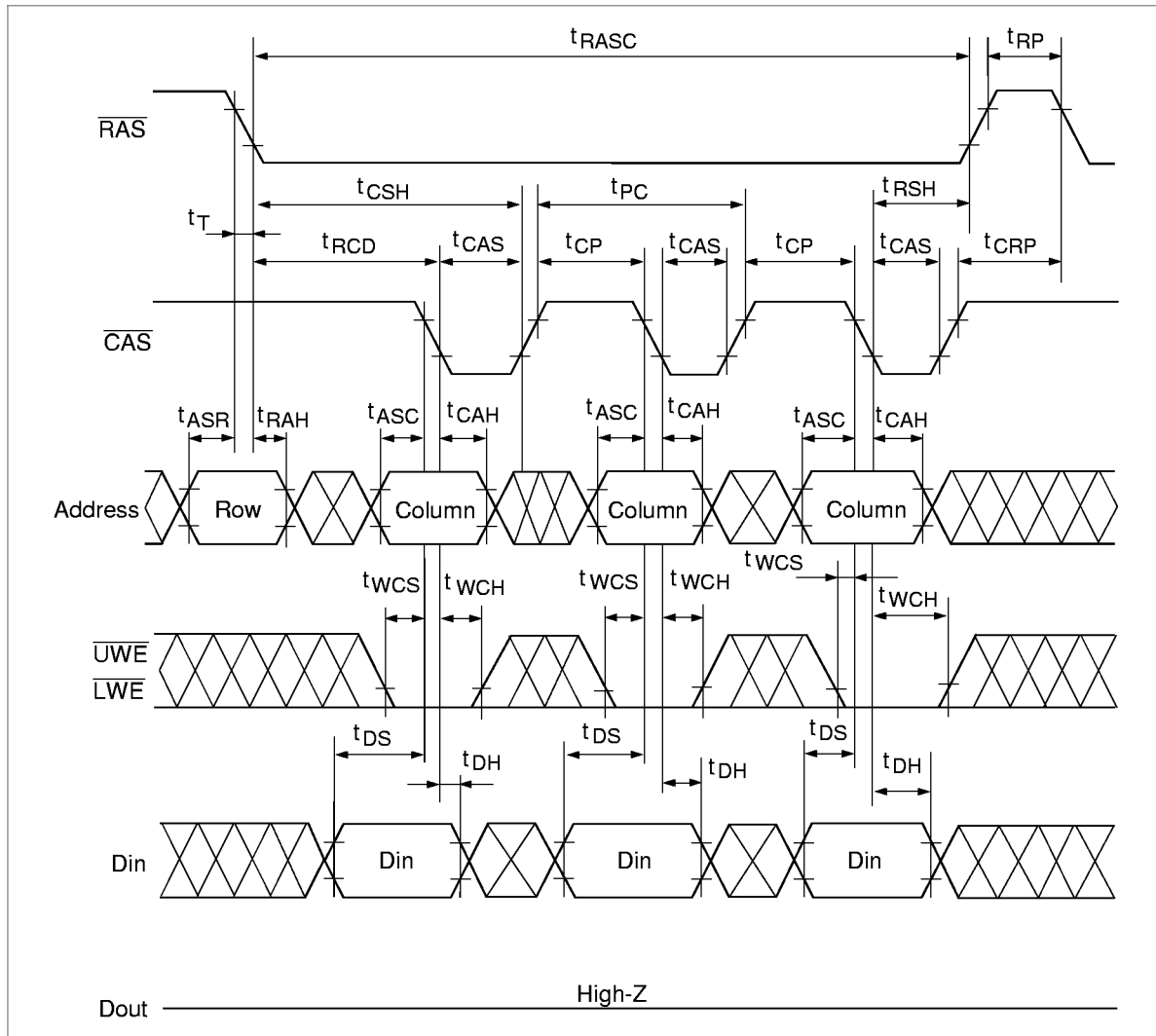


Fast Page Mode Read Cycle

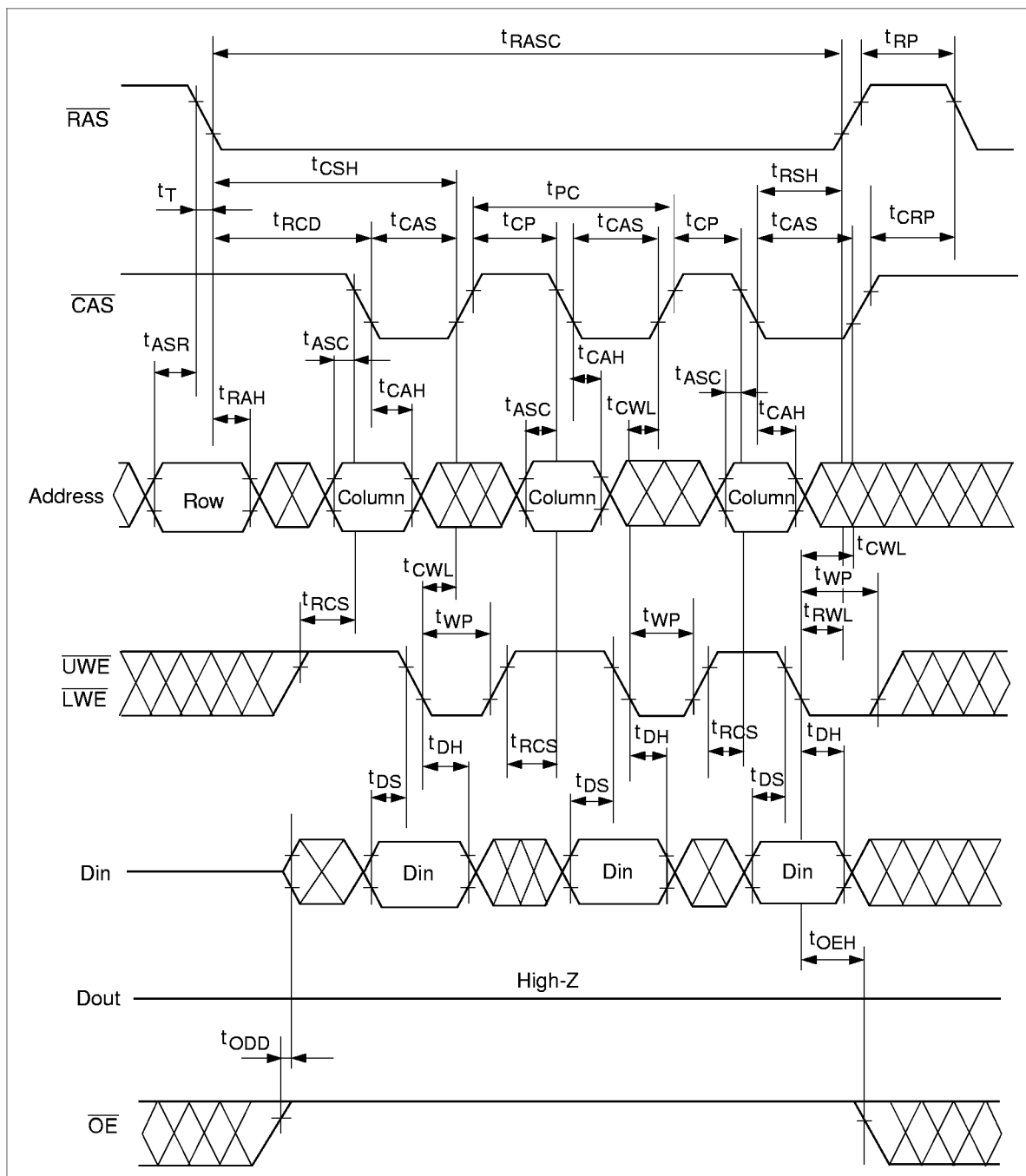


HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

Fast Page Mode Early Write Cycle

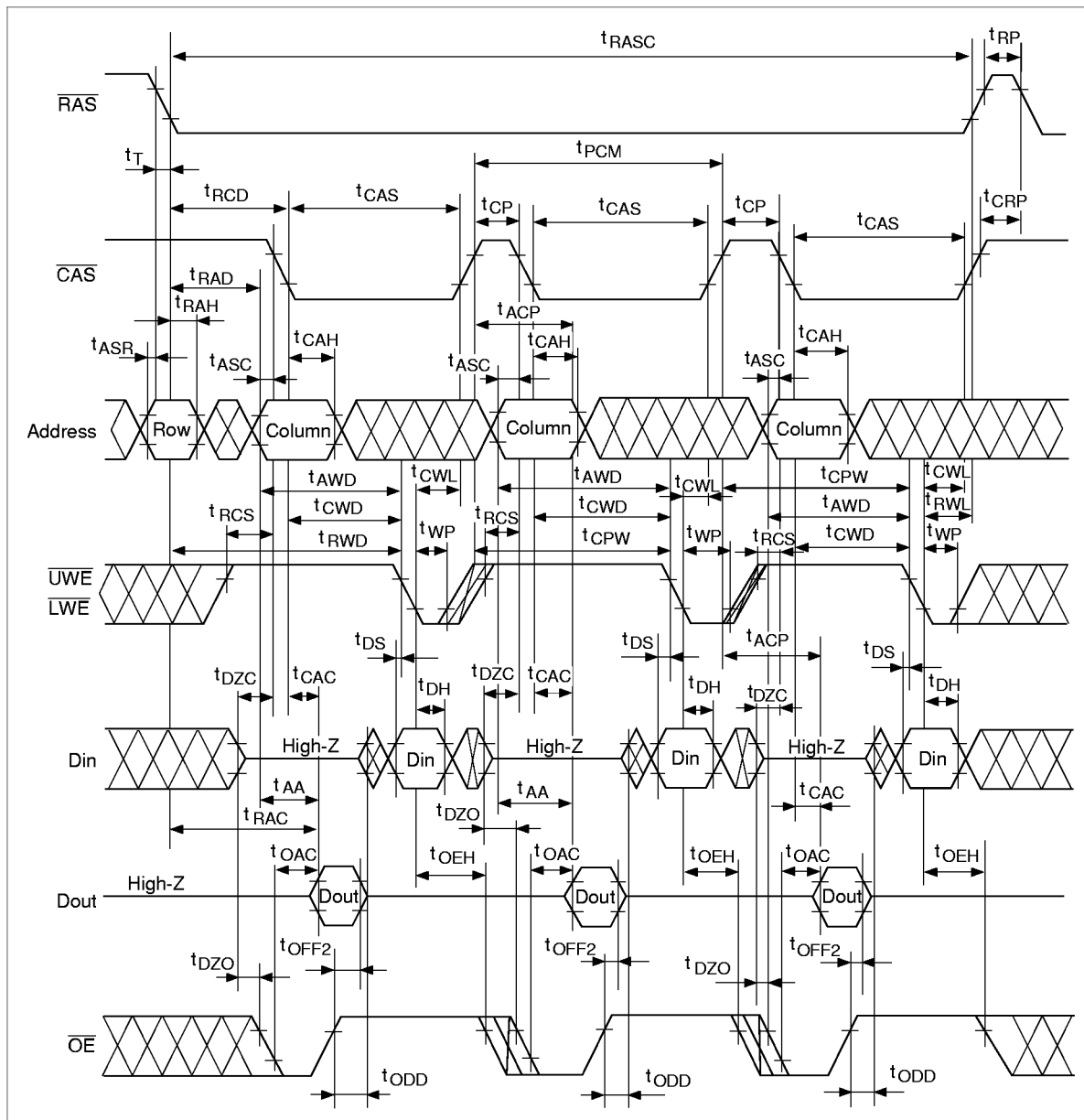


Fast Page Mode Delayed Write Cycle



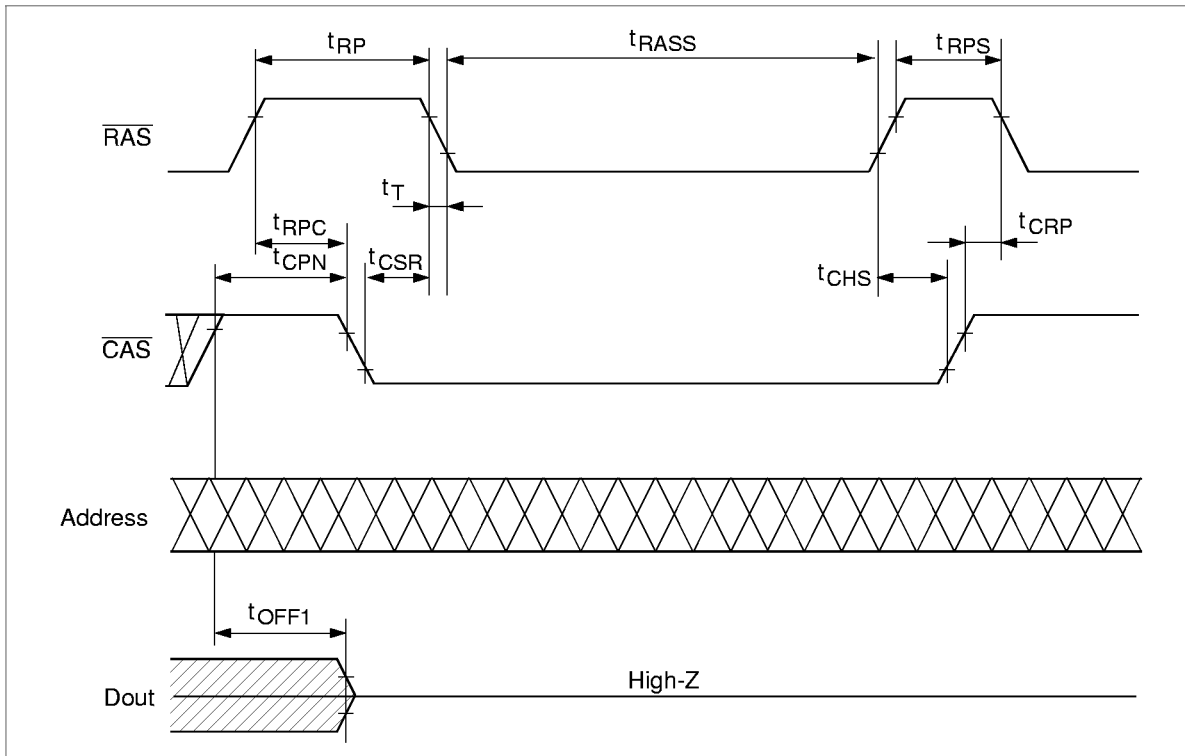
HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

Fast Page Mode Read-Modify-Write Cycle



HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

Self Refresh Cycle*23, 24, 25, 26



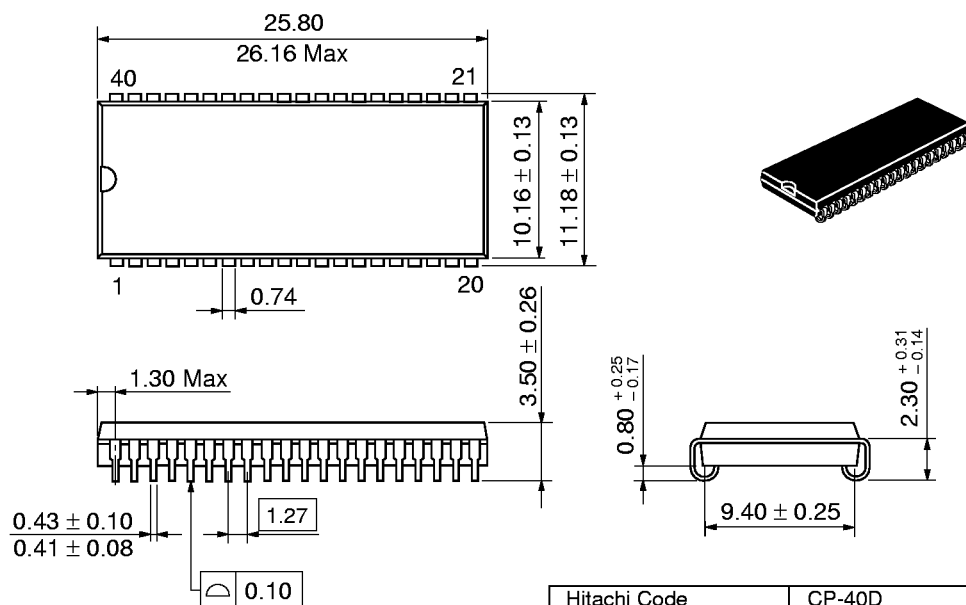
HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

Package Dimensions

HM514170DJ/DLJ, HM514270DJ/DLJ Series

HM51S4170DJ/DLJ, HM51S4270DJ/DLJ Series (CP-40D)

Unit: mm



Dimension including the plating thickness
Base material dimension

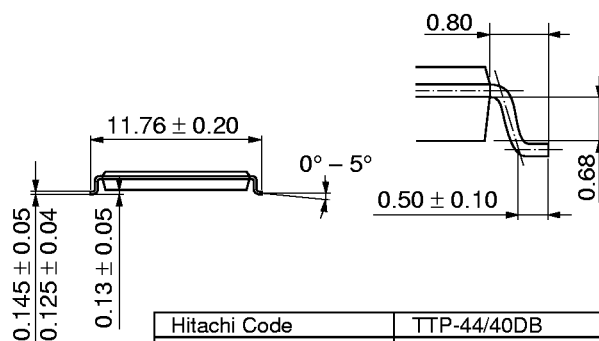
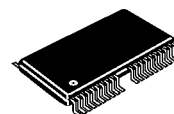
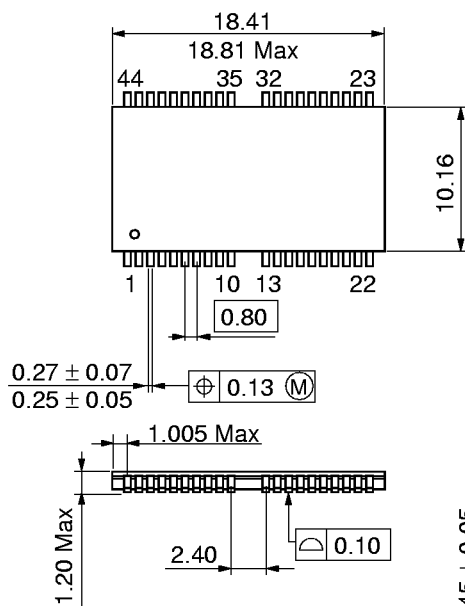
Hitachi Code	CP-40D
JEDEC Code	—
EIAJ Code	SC-640
Weight (reference value)	1.73 g

HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

HM514170DTT/DLTT, HM514270DTT/DLTT Series

HM51S4170DTT/DLTT, HM51S4270DTT/DLTT Series (TTP-44/40DB)

Unit: mm



Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-44/40DB
JEDEC Code	MO-133BA
EIAJ Code	SC-504-8C
Weight (reference value)	0.43 g

HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

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HM514170D, HM514270D Series, HM51S4170D, HM51S4270D Series

Revision Record

Rev.	Date	Contents of Modification	Drawn by	Approved by
0.0	Oct. 18, 1996	Initial issue	H. Hisakawa	S. Suzuki
1.0	Jul. 10, 1997	Operation table Addition of OE input Correct errors Power dissipation 825/660/578 mW to 743/660/578 mW (HM51(S)4170D Series) AC Characteristics Correct note 19: addition of t_{RPC} , t_{CSR} Correct note 20: addition of t_{CHR} Timing waveforms CAS-before-RAS refresh cycle Read-modify-write cycle, Fast page mode read-modify-write cycle		
